

低消費電力SRAM 発注型名

R1 L V 5256 E SA - 5 S I #B1

R1 L P 04 08 D SP - 5 S I #B1

RM L V 04 16 E G SB - 4 S 2 #A A 1

RENESAS Memory

Chip configuration

| | |
|----------|---------------------|
| L | LPSRAM, Single chip |
| W | LPSRAM, Two chips |

Operating Voltage

| | |
|----------|----|
| V | 3V |
| P | 5V |

Memory Density

| | |
|-------------|------------|
| 5256 | 256Kb (x8) |
| 01 | 1Mb |
| 02 | 2Mb |
| 04 | 4Mb |
| 08 | 8Mb |
| 16 | 16Mb |
| 32 | 32Mb |
| 64 | 64Mb |

Bus Width

| | |
|-----------|-----|
| 08 | x8 |
| 16 | x16 |

Chip Generation

Industrial Grade

Package Type

| | |
|-----------|---|
| SA | TSOP-I (256Kb/8Mb/16Mb/32Mb/64Mb) sTSOP (1Mb/2Mb/4Mb) |
| SB | TSOP-II |
| SD | μTSOP |
| SF | TSOP-I (1Mb) |
| SP | SOP (256Kb, 4Mb) |
| SN | SOP (1Mb) |
| BG | FBGA |

Packing, Environmental

| | | |
|------------------|------------------|---------------|
| | Packing | Environmental |
| #B0 / #B1 | Tray or Magazine | Pb free |
| #S0 / #S1 | Tape & Reel | Pb free |

Assembly Site Rev. , etc.

| | |
|----------|-----------|
| 0 | Rev. Code |
| 1 | Rev. Code |

Environment

| | |
|----------|--------------------------------|
| A | Pb free (pure-Tin plating) |
| C | Pb free (non pure-Tin plating) |

Packing

| | |
|----------|-----------------------------------|
| A | Tray |
| C | Magazine |
| H | Tape & Reel (TSOP-II, uTSOP, SOP) |
| K | Tape & Reel (FBGA, TSOP-I, sTSOP) |

Operating Temperature

| | |
|----------|------------------|
| R | 0 to 70 deg. C |
| I | -40 to 85 deg. C |
| 2 | -40 to 85 deg. C |

Access time

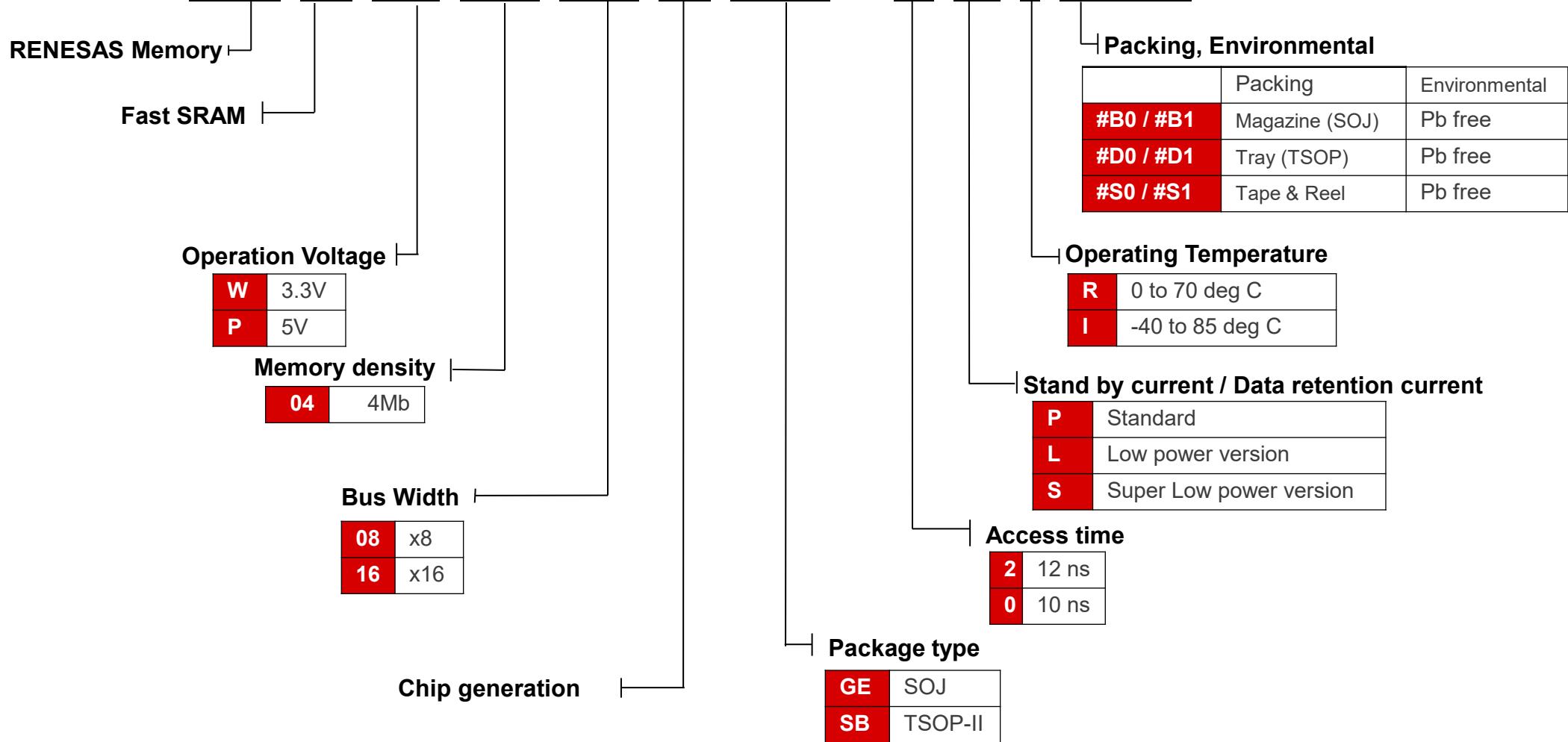
| | |
|----------|-------|
| 5 | 55 ns |
| 4 | 45 ns |

Stand-by current / Data retention current

| | |
|----------|-------------------------|
| S | Low power version |
| U | Ultra Low power version |

高速 4Mb SRAM 発注型名

R1 R W 04 16 D SB - 2 P I #D1



Example shown here: Part number R1RW0416DSB-2PI#D1